

# NPN RF POWER TRANSISTOR

**DESCRIPTION:**

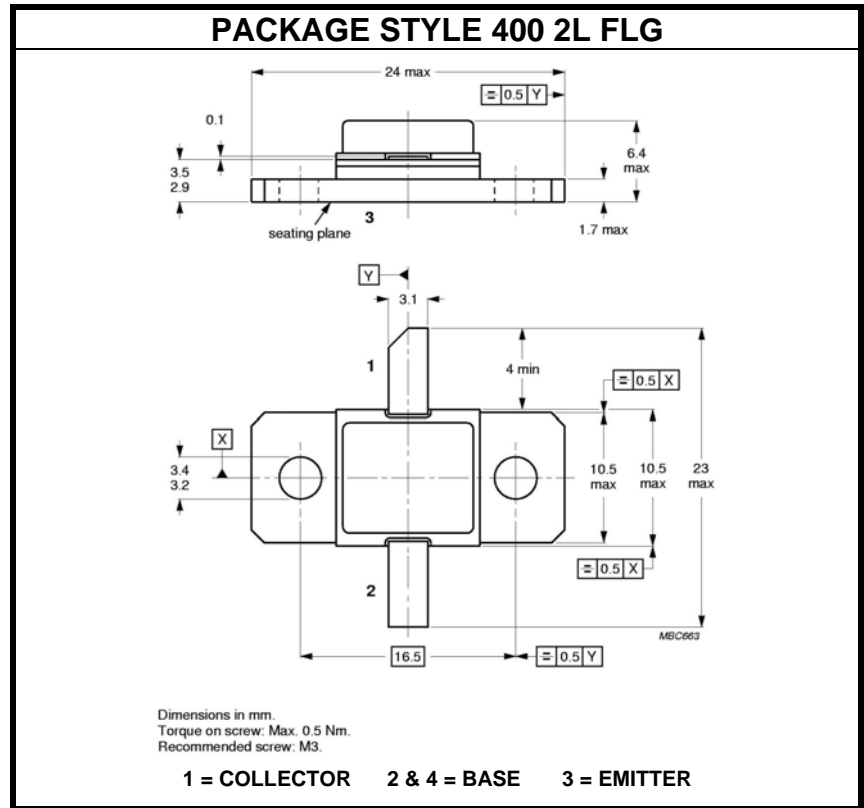
The **AM82731** is a Common Base Device Designed for Pulsed S-Band Radar Amplifier Applications.

**FEATURES INCLUDE:**

- Input/Output Matching
- Gold Metallization
- Emitter Ballasting

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	0.9 A
<b>V<sub>CBO</sub></b>	50 V
<b>P<sub>DISS</sub></b>	27 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-55 °C to +200 °C
<b>T<sub>STG</sub></b>	-55 °C to +200 °C
<b>θ<sub>JC</sub></b>	6.5 °C/W


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CBO</sub></b>	I <sub>C</sub> = 2.0 mA	50			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 2.0 mA	50			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>CE</sub> = 2.0 mA			2.0	<b>mA</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 1.0 mA	3.5			<b>V</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5 V    I <sub>C</sub> = 200 mA	10			<b>---</b>
<b>P<sub>G</sub></b>	V <sub>CE</sub> = 30 V    P <sub>OUT</sub> = 3.0 W    f = 2700 to 3100 MHz	5.7	6.5		<b>dB</b>
<b>η<sub>C</sub></b>	Pulse Width = 100 μS    Duty Cycle = 10%		35		<b>%</b>